

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Original) A semiconductor device mounting a film-like integrated circuit that is formed by separating an integrated circuit formed over a substrate from the substrate.
2. (Original) A semiconductor device according to claim 1, wherein a thickness of a semiconductor layer constituting the integrated circuit is from 30 nm to 60 nm.
3. (Original) A semiconductor device according to claim 1, wherein a film of which thermal conductivity is 10 W/m · K or more is provided in order to be in contact with the film-like integrated circuit.
4. (Currently Amended) A semiconductor device according to ~~any one of claims~~ claim 1, wherein the film-like integrated circuit is electrically connected to a wiring board by a protruding electrode.
5. (Original) A semiconductor device according to claim 4, wherein the wiring board includes a plurality of film-like integrated circuits.
6. (Original) A semiconductor device mounting an integrated circuit including a plurality of semiconductor layers separated in island-like,  
wherein a thickness of the semiconductor layer is from 30 nm to 60 nm.

7. (Original) A semiconductor device according to claim 6, wherein a film of which thermal conductivity is  $10 \text{ W/m} \cdot \text{K}$  or more is provided in order to be in contact with the integrated circuit film.

8. (Original) A semiconductor device according to claim 6, wherein the integrated circuit film is electrically connected to a wiring board by a protruding electrode.

9. (Original) A semiconductor device according to claim 8, wherein the wiring board includes the plurality of integrated circuit films.

10. (Original) A semiconductor device according to claim 6, wherein the integrated circuit film is polygon.

11. (Original) A method for manufacturing a semiconductor device comprising the steps of:

forming a crystalline semiconductor film over a first substrate;  
forming an element using the crystalline semiconductor film, a wiring for transmitting an electrical signal to the element, and an element layer comprising an insulating film;  
transferring the element layer from the first substrate to a second substrate;  
transferring the element layer to a sheet; and  
manufacturing an integrated circuit film by separating the element layer.

12. (Original) A method for manufacturing a semiconductor device according to claim 11,

wherein the element layer is formed, and then a protruding electrode for transmitting an electrical signal to the wiring is formed before transferring the element layer to the second substrate.

13. (Original) A method for manufacturing a semiconductor device according to claim 7, wherein a film of which thermal conductivity is  $10 \text{ W/m} \cdot \text{K}$  or more is formed over the element layer after transferring the element layer to the second substrate.

14. (Original) A method for manufacturing a semiconductor device according to claim 12, wherein a film of which thermal conductivity is  $10 \text{ W/m} \cdot \text{K}$  or more is formed over the element layer after transferring the element layer to the second substrate.